

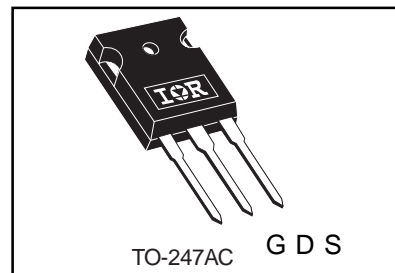
## Applications

- Switch Mode Power Supply ( SMPS )
- Uninterruptable Power Supply
- High speed power switching

$V_{DSS}$	$R_{ds(on)}$ max	$I_D$
500V	0.23W	22A

## Benefits

- Low Gate Charge  $Q_g$  results in Simple Drive Requirement
- Improved Gate, Avalanche and dynamic  $dv/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D$ @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	22	A
$I_D$ @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	14	
$I_{DM}$	Pulsed Drain Current ①	88	
$P_D$ @ $T_C = 25^\circ\text{C}$	Power Dissipation	277	W
	Linear Derating Factor	2.2	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	4.8	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

## Applicable Off Line SMPS Topologies:

- Full Bridge Converters
- Power Factor Correction Boost

# IRFP22N50A

Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.23	$\omega$	$V_{GS} = 10V, I_D = 13A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 400V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	12	—	—	S	$V_{DS} = 50V, I_D = 13A$
$Q_g$	Total Gate Charge	—	—	120	nC	$I_D = 22A$
$Q_{gs}$	Gate-to-Source Charge	—	—	32		$V_{DS} = 400V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	52		$V_{GS} = 10V$ , See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	26	—		$V_{DD} = 250V$
$t_r$	Rise Time	—	94	—	ns	$I_D = 22A$
$t_{d(off)}$	Turn-Off Delay Time	—	47	—		$R_D = 4.3\omega$
$t_f$	Fall Time	—	47	—		$R_D = 11\omega$ , See Fig. 10 ④
$C_{iss}$	Input Capacitance	—	3450	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	513	—		$V_{DS} = 25V$
$C_{riss}$	Reverse Transfer Capacitance	—	27	—		$f = 1.0\text{MHz}$ , See Fig. 5
$C_{oss}$	Output Capacitance	—	4935	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	137	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	264	—		$V_{GS} = 0V, V_{DS} = 0V$ to 400V ⑤

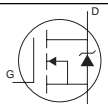
## Avalanche Characteristics

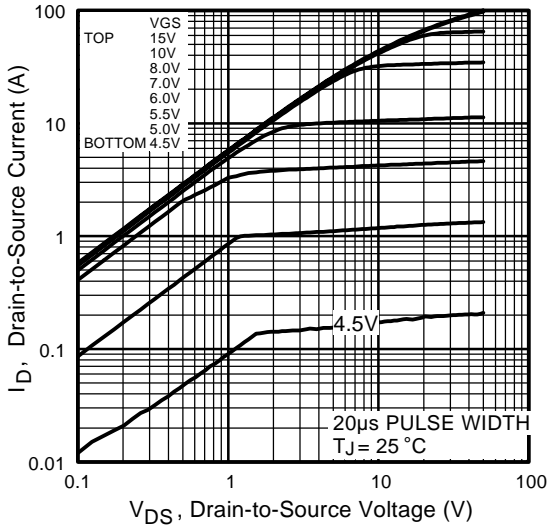
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	1180	mJ
$I_{AR}$	Avalanche Current①	—	22	A
$E_{AR}$	Repetitive Avalanche Energy①	—	28	mJ

## Thermal Resistance

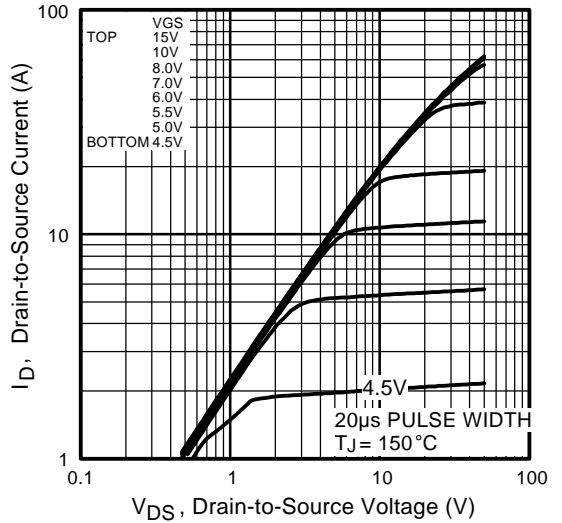
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.45	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	40	

## Diode Characteristics

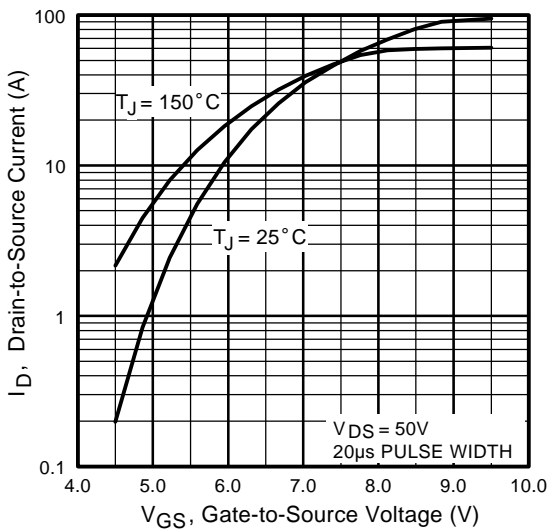
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	22	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	88		
$V_{SD}$	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 22A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	570	850	ns	$T_J = 25^\circ\text{C}, I_F = 22A$
$Q_{rr}$	Reverse Recovery Charge	—	6.1	9.2	$\mu\text{C}$	$di/dt = 100A/\mu\text{s}$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				



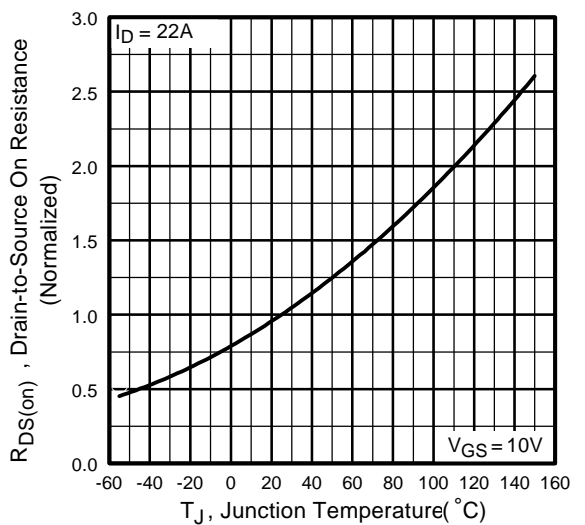
**Fig 1.** Typical Output Characteristics



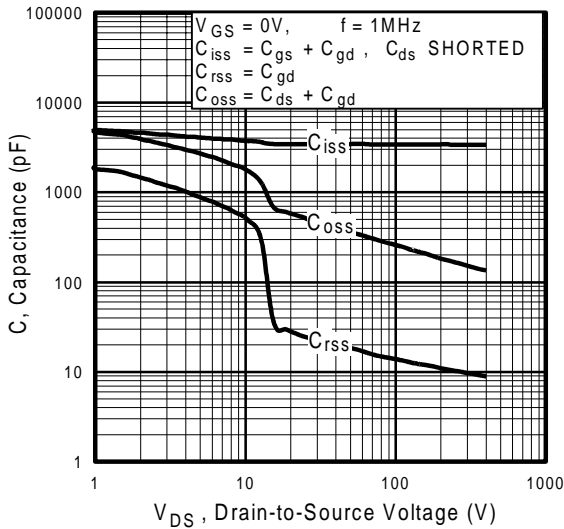
**Fig 2.** Typical Output Characteristics



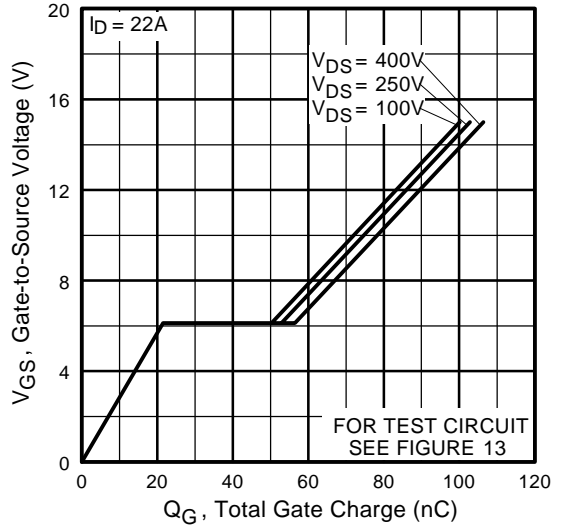
**Fig 3.** Typical Transfer Characteristics



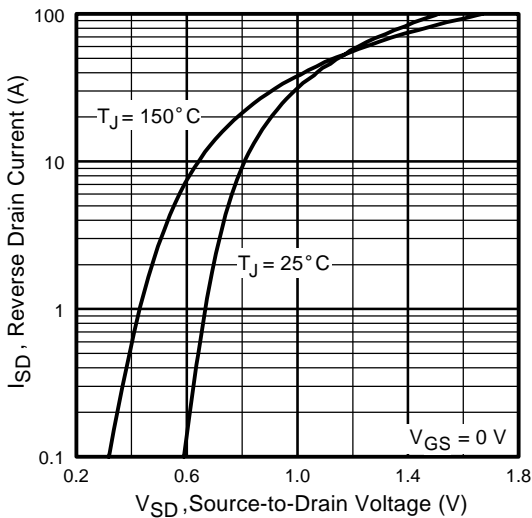
**Fig 4.** Normalized On-Resistance Vs. Temperature



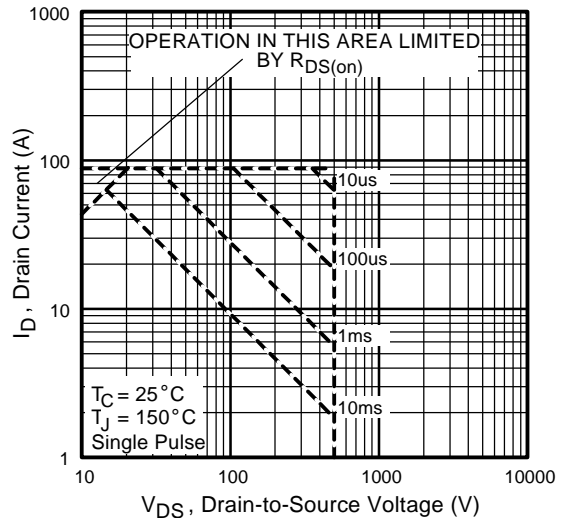
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



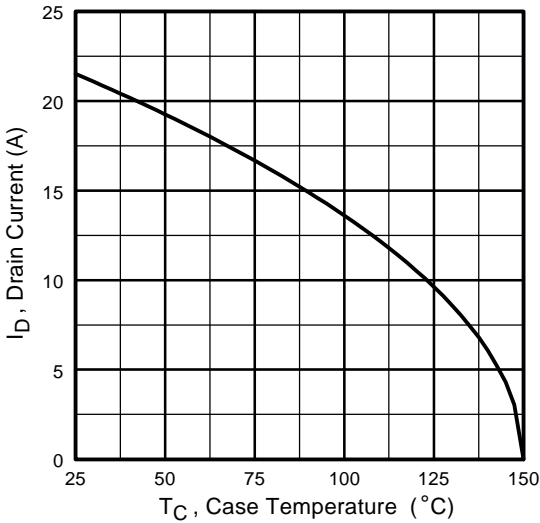
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



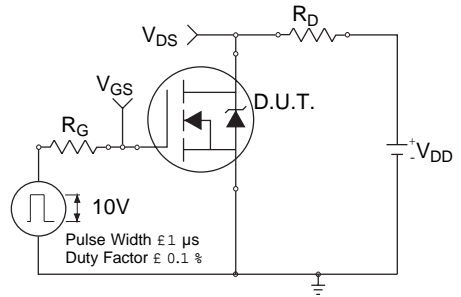
**Fig 7.** Typical Source-Drain Diode Forward Voltage



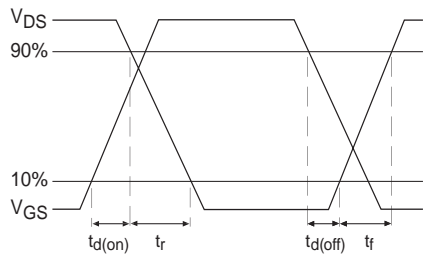
**Fig 8.** Maximum Safe Operating Area



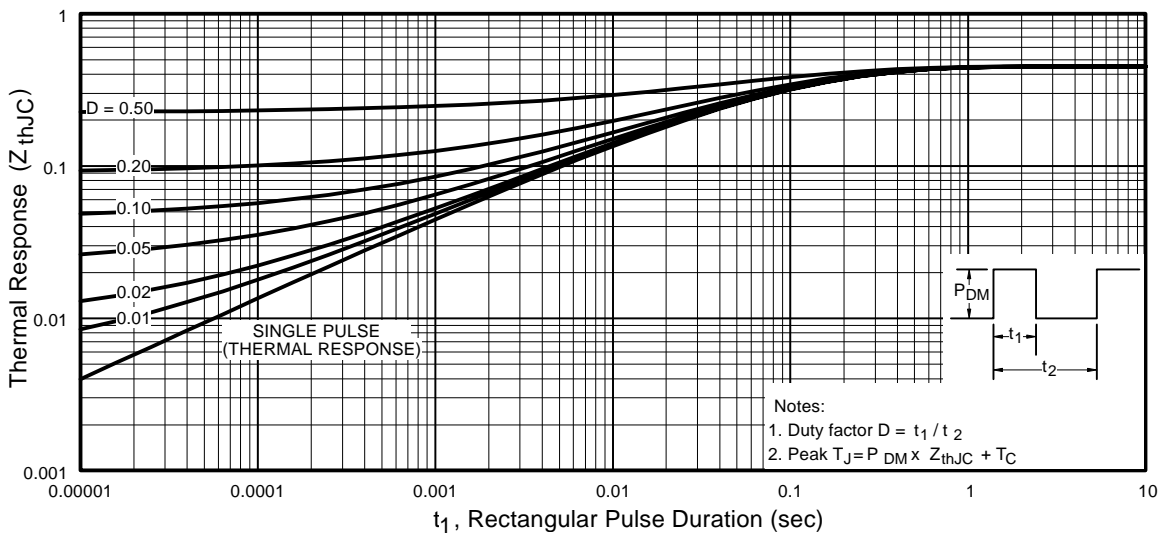
**Fig 9.** Maximum Drain Current Vs. Case Temperature



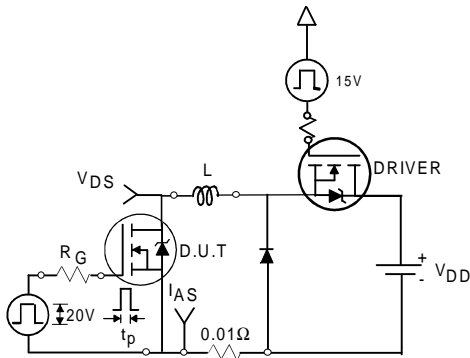
**Fig 10a.** Switching Time Test Circuit



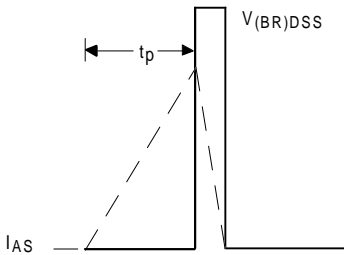
**Fig 10b.** Switching Time Waveforms



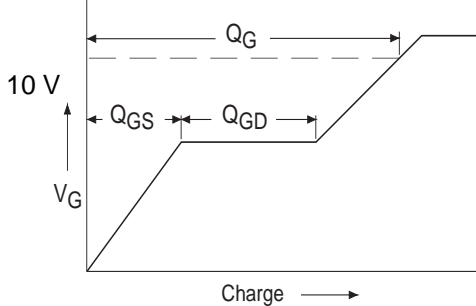
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



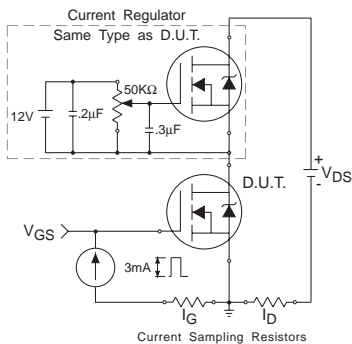
**Fig 12a.** Unclamped Inductive Test Circuit



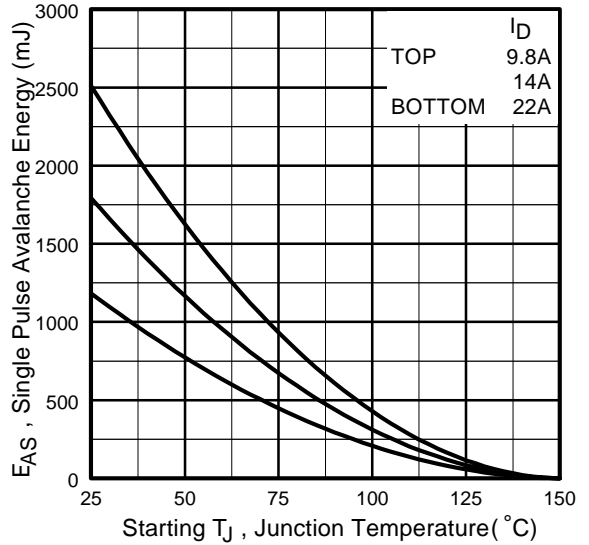
**Fig 12b.** Unclamped Inductive Waveforms



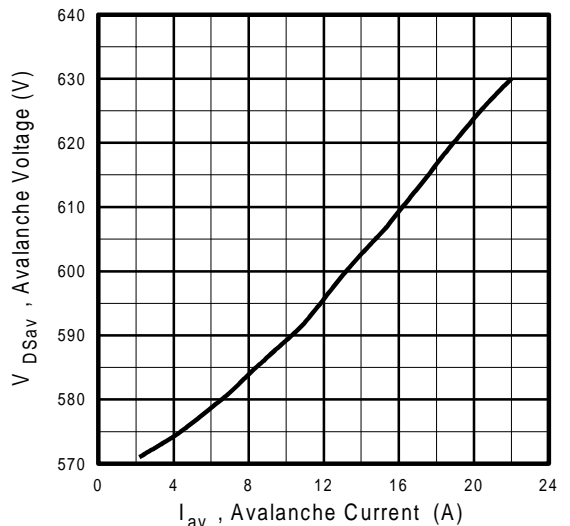
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

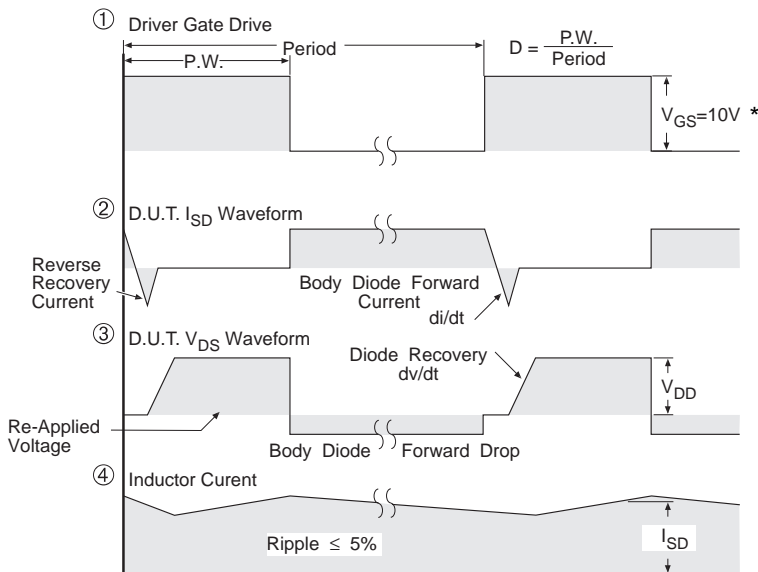
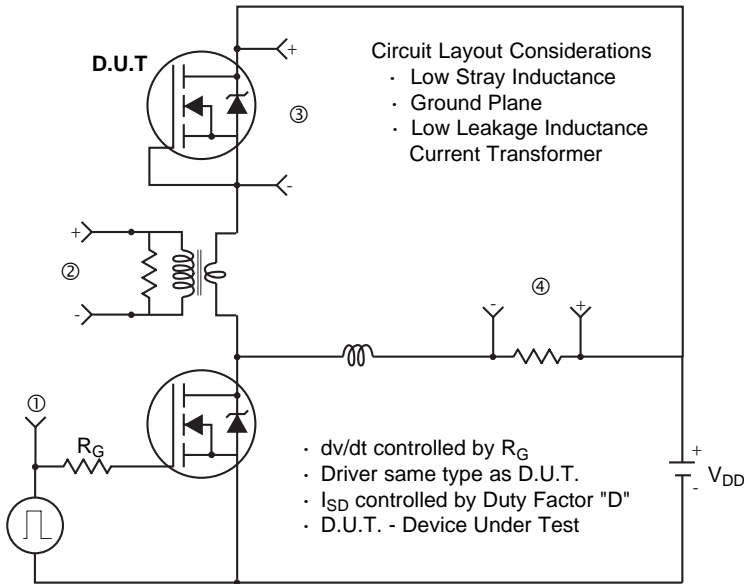


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 12d.** Typical Drain-to-Source Voltage Vs. Avalanche Current

## Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

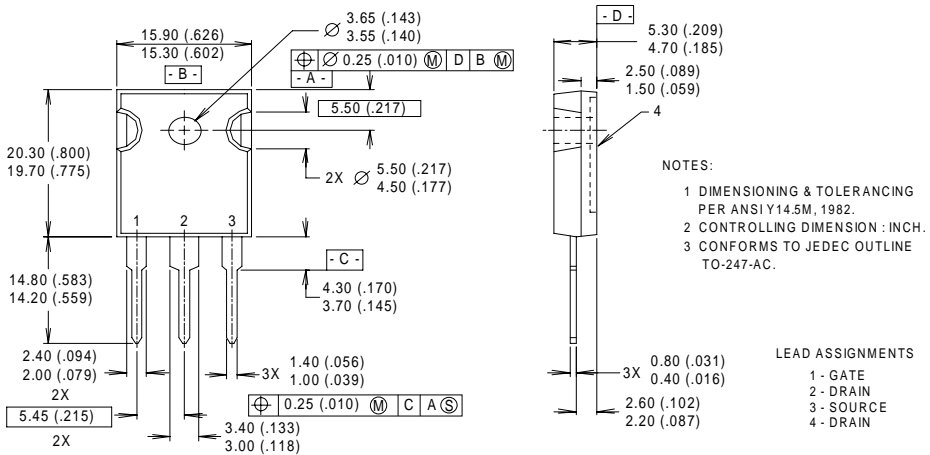
**Fig 14.** For N-Channel HEXFETS

# IRFP22N50A

## Package Outline

### TO-247AC Outline

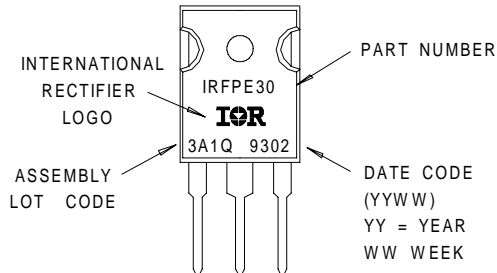
Dimensions are shown in millimeters (inches)



## Part Marking Information

### TO-247AC

EXAMPLE : THIS IS AN IRFPE30  
WITH ASSEMBLY  
LOT CODE 3A1Q



### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 4.87\text{mH}$   
 $R_G = 25\text{m}\Omega$ ,  $I_{AS} = 22\text{A}$ . (See Figure 12)
- ③  $I_{SD} \leq 22\text{A}$ ,  $di/dt \leq 190\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$